

SPTECH Silicon NPN Darlington Power Transistor MN638S

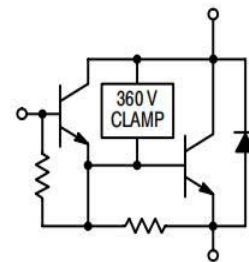
DESCRIPTION

- Low Collector Saturation Voltage
- High DC Current Gain
- High Reliability

APPLICATIONS

- Audio power amplifiers
- Relay & solenoid drivers
- Motor controls
- General purpose power amplifiers
- Including zener diode

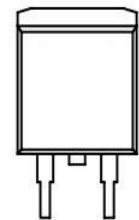
**AUTOPROTECTED
DARLINGTON
10 AMPERES
360-450 VOLTS CLAMP
150 WATTS**



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	450	V
V _{CEO(SUS)}	Collector-Emitter Voltage	350	V
V _{EBO}	Emitter-Base Voltage	6	V
V _Z	Zener Voltage	350	V
I _C	Collector Current-Continuous	10	A
I _B	Base Current-Continuous	3.0	A
P _C	Collector Power Dissipation @ T _C =25°C	150	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-40~150	°C

MARKING DIAGRAM



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.0	°C/W

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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _Z	Zener Voltage	I _Z = 0.1mA	350		450	V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 5mA; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 15mA			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4A; I _B = 15mA			2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 350V; I _E = 0			0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C =0			5	mA
h _{FE}	DC Current Gain	I _C = 4A; V _{CE} = 5V	500		4000	